

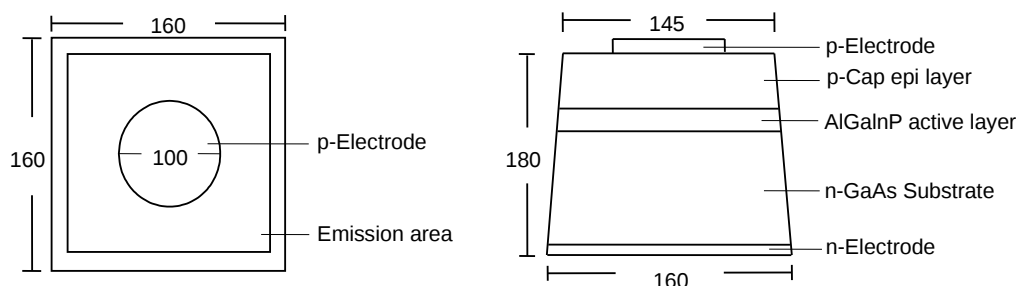
■ Features :

- MOVPE Epi Wafer
- Low Cost

■ Typical Applications :

- Replace VPE
- Dot Matrix
- Lamp Display
- High Performance X'mas Lamps

■ Outline Dimensions : (Unit: μm)



■ Physical Structure :

Chip dimension	Chip size	160 μm x 160 μm
	Thickness	180 μm
	Emission area	145 μm
	Bonding pad	100 μm
Electrode	Top: P (anode)	Aluminum (Gold optional)
	Backside: N (cathode)	Gold alloy
Surface condition	Not frosted	

■ Electro-Optical Characteristics : ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Forward Voltage	V_F	$I_F = 20 \text{ mA}$	-	2.10	2.40	V
Reverse Voltage	V_R	$I_R = 10 \text{ uA}$	5	-	-	V
Wavelength	λ_p	$I_F = 20 \text{ mA}$	-	630	-	nm
	λ_D		620	625	630	
Spectral width at half height	$\Delta\lambda$	$I_F = 20 \text{ mA}$	-	20	-	nm
Luminous Intensity	I_v	$I_F = 20 \text{ mA}$	60	-	-	mcd
			80			
			100			
			120			

■ Typical Electro-Optical Characteristics Curve:

Fig 1. Forward Current vs. Forward Voltage

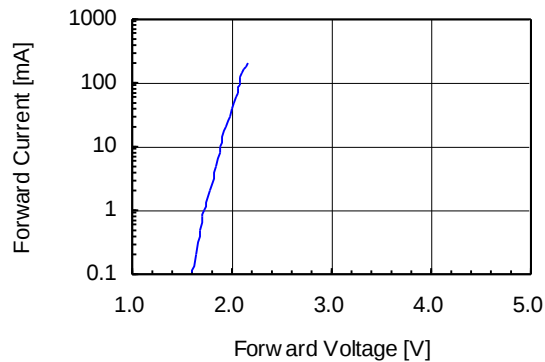


Fig 2. Relative Intensity vs. Forward Current

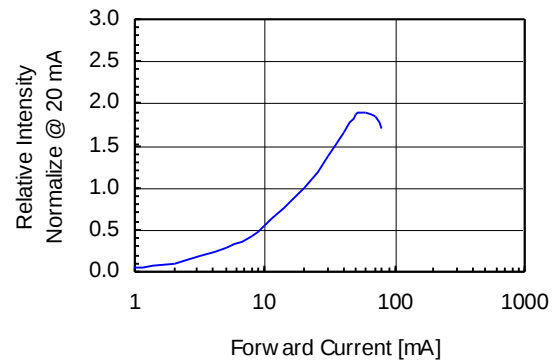


Fig 3. Forward Voltage vs. Temperature

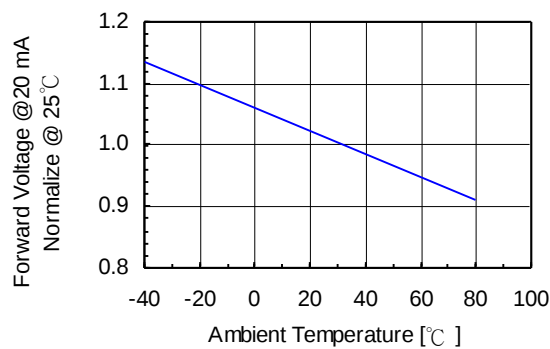


Fig 4. Relative Intensity vs. Temperature

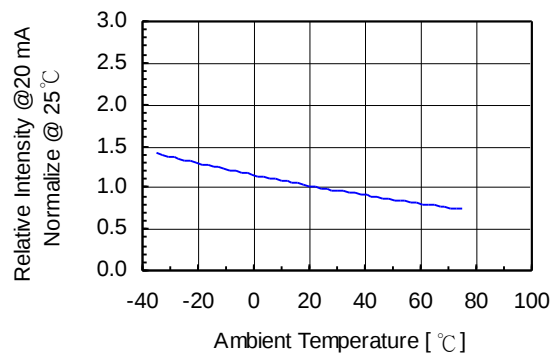


Fig 5. Relative Intensity vs. Wavelength

